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Published Version

Peer-review status of attached file:
Peer-reviewed

Citation for published item:

Further information on publisher’s website:
http://dx.doi.org/10.1063/1.2162263

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Multimode switching induced by a transverse field in planar magnetic nanowires

M. T. Bryan  
Department of Engineering Materials, University of Sheffield, S1 3JD, United Kingdom

D. Atkinson  
Department of Physics, University of Durham, DH1 3LE, United Kingdom

D. A. Allwood  
Department of Engineering Materials, University of Sheffield, S1 3JD, United Kingdom

(Received 19 September 2005; accepted 17 November 2005; published online 17 January 2006)

We report how transverse fields affect the axial field needed to “inject” domain walls from a large Permalloy (Ni$_{80}$Fe$_{20}$) pad into planar nanowires of width 184 nm, 303 nm, 321 nm, and 537 nm fabricated by electron beam lithography. For the narrowest wire, different switching fields are observed under the same transverse field conditions, indicating that more than one mode or state for the domain walls may exist. In contrast, in the widest wires a transverse field causes each reversal event to occur in two stages. The different response may be attributed to the magnetostatic energy differences of domain walls in wires of different widths. © 2006 American Institute of Physics.

[DOI: 10.1063/1.2162263]

Research into the behavior of magnetic structures with key dimensions deep into the submicron regime has developed rapidly in recent years as such structures present opportunities to study underlying physical processes, as well as being of interest for potential technological applications. For elongated planar structures, reversal via the propagation of head-to-head or tail-to-tail domain walls has been understood through micromagnetic modeling and domain wall propagation experiments. Domain wall propagation can be controlled using structures with a larger area pad of magnetic material connected to a narrower nanowire of interest. Such structures have been widely used for “injecting” domain walls into nanostructures.

More recently, the presence of metastable magnetization states has emerged as a significant issue even in simple magnetic nanostructures. Experiments have shown that switching can be complex, with reversal dependent on the metastable magnetization configurations in rectangular and elliptical Permalloy structures subject to short axis fields. In other investigations, electrical measurements and magnetic force microscopy (MFM) have shown that a domain wall can be pinned in a variety of different states at a notch in an elongated structure. It has also been observed that multiple temperature-dependent switching fields can occur in a wire and pad structure with an oblique field. Controlling such multiple modes is important for potential applications since reliable switching and a narrow switching-field distribution can be critical requirements for device operation.

Here we report the effect of transverse field on the magnetization reversal behavior of planar Permalloy nanowires which have a large nucleation pad at one end. The pad can generate magnetic domain walls that are injected into the narrower nanowire structure during the switching process. L-shaped Permalloy (Ni$_{80}$Fe$_{20}$) planar nanowires were fabricated on a thermally oxidized silicon substrate with a gold underlayer by electron beam lithography and metallization using thermal evaporation followed by resist lift-off. At one end of each nanowire, a larger rectangular nucleation pad of Permalloy was fabricated. The other end was pointed to suppress domain wall nucleation, and resultant domain wall motion from this end. The four L-shaped wires studied had widths of 184 nm, 303 nm, 321 nm, and 537 nm, as measured by scanning electron microscopy (SEM). Each nucleation pad was 1.5 μm wide × 15 μm long. The structures were all 8 nm thick. The L-shape geometry was developed to study domain wall behavior more generally and is not strictly needed in these experiments.

Axial magnetization reversal was detected using a magneto-optical Kerr effect (MOKE) magnetometer, capable of detecting “single-shot” switching events, although most measurements involve averaging of many field cycles to improve the signal to noise ratio. The switching behavior of both the nanowires and the associated nucleation pads were measured separately in the presence of different combinations of orthogonal magnetic fields applied within the plane of the magnetic structures, at room temperature. Figure 1 shows schematically the geometry of the samples, the orientation of magnetic fields $H_x$ and $H_y$, and the MOKE laser beam location used in the measurements. $H_x$ and $H_y$ were applied at 27 Hz with an amplitude of 116 Oe and $H_y^0$, respectively. MOKE measurements were sensitive to switching

![FIG. 1. A schematic of the nanowire structure showing the magnetic fields ($H_x$ and $H_y$) and the magnetization states as a function of the counterclockwise rotating magnetic field from (a) to (d). The laser spot position for the MOKE measurements is indicated by the dotted ellipse in (a). DW denotes the domain wall position when a wall is present. Not to scale.](image-url)
along the \( H_x \) axis. The phase of \( H_x \) (the transverse field) was shifted by \( \pi/2 \) with respect to \( H_y \) in order to generate a field vector (of varying amplitude) at the sample that rotated counterclockwise. A domain wall is formed at the junction between the pad and the wire when the pad magnetization is reversed [Fig. 1(b)]. As \( H_y \) increases, the wall propagates through to the corner and switches the horizontal arm of the nanowire [Fig. 1(c)]. As the field vector sweeps into the positive \( y \)-direction the wall is swept up through vertical section of the structure to complete the magnetization reversal [Fig. 1(d)]. In the subsequent part of the cycle, the process is repeated but this time the fields and the magnetization change have the opposite sign. In this way the reversal is always initiated from the nucleation pad and the domain wall is swept up the vertical section of the wire. Only for the counterclockwise rotating field do both switching events in the hysteresis loops represent reversal by domain walls propagating from the junction of the pad and wire. When \( H_y = 0 \) or if a static field were applied along the \( y \)-axis, the reversal of an initially continuous magnetization will leave a domain wall at the corner of the structure. This wall can then propagate back towards the pad when the sign of \( H_x \) is reversed. Therefore, with \( H_y = 0 \) Oe or a static \( y \)-axis field, only one side of the hysteresis loop represents reversal by domain walls propagating from the junction of the pad and wire. Switching using static fields was consistent with the results using the counterclockwise rotating field.

Figure 2 shows normalized axial MOKE hysteresis loops for 184 nm and 534 nm wide wires as a function of transverse fields with \( H_y = 0 \) Oe, 34 Oe, 45 Oe, and 77 Oe, respectively. The loops are averaged over several hundred field cycles. For the 184 nm wire with \( H_y = 0 \) Oe [Fig. 2(a)], the switching behavior is different under positive and negative fields, with a sharp switching event at negative fields and more slowly varying reversal at positive fields. This indicates that the laser spot is close to the corner and the switching is consistent with sharp switching from the pad at negative fields and back propagation of an existing wall from the corner at positive fields, as has been observed previously.15

Interestingly, when a moderate transverse field is applied [Fig. 2(b)], the switching transition occurs in multiple steps, with clear transitions around 42 Oe and 73 Oe. At higher transverse fields the switching becomes asymmetric with two steps at negative field and a single step at positive fields [Fig. 2(c)]. At still higher transverse fields [Fig. 2(d)], single-step magnetization reversal returns, but switching is sharper and at a lower field (35 Oe). By comparison, Figs. 2(e)–2(h) show similarly averaged axial hysteresis loops from a 537 nm wide wire. In the wider wire, two-step switching develops and becomes more pronounced at higher transverse fields [Figs. 2(g) and 2(h)], but not at lower fields [Figs. 2(e) and 2(f)]. Intermediate wire widths show aspects of both types of behavior, with reversal behavior more similar to the 537 nm wire for the wider wires.

In order to ascertain the nature of the multistep switching observed in the averaged loops, the MOKE magnetometer was set up to measure switching during a single field sweep. Figures 3(a) and 3(b) show two separate “single-shot” magnetization loops obtained from the 184 nm wide wire with \( H_y = 23 \) Oe. The loops have a low signal-to-noise ratio as no averaging has taken place, but single switching events can still be seen in both loops. However, the switching events occur at markedly different fields of \( \pm 42 \) Oe [Fig. 3(a)] and \( \pm 78 \) Oe [Fig. 3(b)], suggesting two different modes for domain wall injection into the wire under nominally the same field conditions. Others loops for this sample showed that the injection mode could change during one field cycle;
shown in Fig. 4 the averaged hysteresis loops of the 184 nm wire as a func-

tional switching may be related to an interaction between the 

pad is rotated more strongly and a single mode domain wall 

applied. At higher transverse fields the magnetization in the 

fields, as observed. This variation may be largely due to the 

behavior of the pad, since the magnetization of the wire de-

have different forms or modes, each with different depinning 

along the transverse 

striction may be affected by the structure of the domain wall. 

There, the modes were identified with temperature-

dependent domain structures within the nucleation pad, al-

though it is interesting to note that the switching field used 

was applied at 30° to the pad-wire axis, so a transverse field 

component was present. Other studies suggest that the 

depinning field and positioning of a domain wall in a con-

striction may be affected by the structure of the domain wall. 

On this basis, and considering that the pad can be saturated 

along the transverse (γ-) axis with a field of about 50 Oe 

while the 184 nm wide wire is not saturated transverse to its 

long axis with fields up to 420 Oe, it is suggested that the 

application of a moderate transverse field leads to a situation 

where the domain wall formed at the pad-wire junction can 

have different forms or modes, each with different depinning 

fields, as observed. This variation may be largely due to the 

behavior of the pad, since the magnetization of the wire de-

viates much less from its long axis when a transverse field is 

applied. At higher transverse fields the magnetization in the 

pad is rotated more strongly and a single mode domain wall 

with a single switching field is obtained. Alternatively, the 

modal switching may be related to an interaction between the 

transverse field and the magnetization within the domain 

wall. A phase diagram of the switching field for each step in 

the averaged hysteresis loops of the 184 nm wire as a func-

tion of the instantaneous value of the transverse field ($H_y$) is 

shown in Fig. 4(a). The switching field of the wire initially 

decreases with increasing transverse field. Then around $H_y$

=10–20 Oe, two modes of reversal occur. The switching 

fields of these modes fall with further increases of the trans-

verse field until the switching abruptly becomes single mode 

again at approximately $H_y=45$ Oe (close to the hard axis 

saturation field of the pad).

The magnetization of the 537 nm wide wire is more sen-

sitive to a transverse magnetic field than the narrowest wire, 

as its transverse saturation field is close to 150 Oe. In 38 

single-shot observations of the switching transitions mea-

sured at high transverse fields, 28 involved a two-step revers-

al similar to that shown in Fig. 3(d). The phase diagram for 

this wire [Fig. 4(b)] shows switching fields at which each 

step in the averaged hysteresis loops occurs. We suggest that 

the change to two-step switching with a large transverse field 

may involve a field-induced transition to a vortex state or 

perhaps a field-induced pinning event at the wire corner due 

to the sign of $H_y$ opposing propagation around the corner at 

the instant of domain wall injection [Fig. 1(c)].

The intermediate width wires display characteristics that 

are similar to both the widest and the narrowest wires, but 

with a smaller separation between the switching branches, 

supporting the interpretation that the shape anisotropy of a 

wire affects the depinning field from the pad-wire junction.

In conclusion, for the narrowest wire, different switching 

fields are observed under the same field conditions. These are 

attributed to different modes or states for the domain walls 

that are formed at the pad-wire junction. In the widest wires 

the transverse field leads to a change from simple switching 

to a vortexlike switching process. The different response may 

be attributed to the magnetostatic energy difference between 

the wide and narrow wires.